Samsung to Introduce 32-Gigabyte Performance-enhancing Memory Module for Servers

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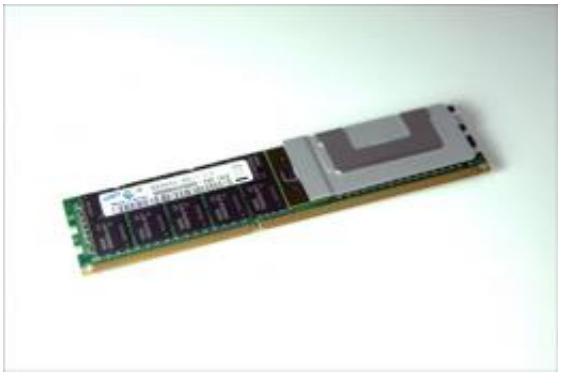

Samsung Electronics announced today that it has developed the industry's first 32 gigabyte (GB) load-reduced, dual-inline memory module (LRDIMM), for server applications.

Samsung will begin mass producing the 32GB LRDIMM in the second half of this year, giving it the largest family of DRAM offerings in the industry.

Using cutting-edge 40 nanometer-class, four gigabit (4Gb) DDR3 chips, which Samsung introduced earlier this year, the new 32GB LRDIMM accommodates next generation servers designed for virtualization, cloud

computing and other high-capacity applications.

“In developing the industry’s first load-reduced module with 40nm-class* DDR3 technology, we are underscoring our determination to combine the best of capacity and performance for the newest generation of servers,” said Dong-Soo Jun, executive vice president, memory marketing, Semiconductor Business, Samsung Electronics.

Samsung’s 32GB LRDIMM prototype consists of 72 4Gb DDR3 chips and an additional memory buffer chip to help reduce the load on the memory subsystem by as much as 75 percent.

By using 32GB LRDIMMs, memory capacity can rise up to 384 gigabytes per CPU. In a two-way server system, capacity can be increased up to 768GB, or about 1.5 times that of a 512GB server system equipped with 32GB DDR3 RDIMMs.

A server equipped with LRDIMMs can process data at 1,333 megabit per second (Mbps), approximately 70 percent faster than the previous speed of 800 Mbps. Samsung’s LRDIMMs operate at 1.35 or 1.5 volts.

Source: Samsung